

Poisson's Equation

* Poisson's Equation derived by S.D. Poisson's. his very popular french mathematician, Engineer and physicist.

Statement:- Poisson's Equation gives the relation-ship between electric potential and charge density in a semiconductor.

or

* The rate of change of carriers concentrations at any point- of semiconductor is given by Poisson's Eqn.

Proof :-

* In case of electrostatics, electric field is Equal to the gradient- of electric potential.

$$\vec{E} = -\nabla V \quad \text{--- (1)}$$

└── gradient ──

where V = electric potential

E = electric field

* we know that- \perp

Gauss-theorem is

• Differential form of Gauss theorem is denoted by

$$\underbrace{\nabla \cdot \vec{E}}_{\text{divergence}} = \frac{\rho}{\epsilon_0} \quad \begin{array}{l} \text{volume charge density} \\ \text{permittivity of free space} \end{array} \quad (1)$$

Above Equation state that, divergence of electric field is equal to the ^{volume} charge density and permittivity of that space.

where —

Now putting the value of \vec{E} in Eqn (1) then we get —

$$\nabla \cdot (-\nabla V) = \frac{\rho}{\epsilon_0}$$

$$\boxed{\nabla^2 V = -\frac{\rho}{\epsilon_0}} \quad (2)$$

scalar
operator

or Laplacian Square

Above Equation is the

Poisson's Eqn for electric statics.

Now Here we ~~are~~ prove the Poisson's Eqn Equation for Semiconductor material so the charge density become —

$$\rho = \rho (-n + p + N_d^+ - N_a^-)$$

Eqn (2) become

$$\vec{\nabla} \cdot \vec{E} = \frac{-\rho}{\epsilon_0} = \frac{\rho(-n + p + N_d^+ - N_a^-)}{\epsilon_0} \quad \text{--- (4)}$$

We know that —

In case of Semiconductor electric field is equal to the rate of change of electric flux so —

$$E = - \frac{d\phi(x)}{dx} \quad \left| \begin{array}{l} \text{electrostatically} \\ E = - \nabla V \end{array} \right.$$

$$E = - \nabla \phi(x) \quad \text{--- (5)}$$

putting the value of E in Eqn (4) and we get —

$$\boxed{\nabla^2 \phi(x) = \frac{\rho(-n + p + N_d^+ - N_a^-)}{\epsilon_0}}$$

This is the poission's Eqn for